



TPV375

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **TPV375** is a Common Emitter Device Designed for Class A Television Band III Applications.

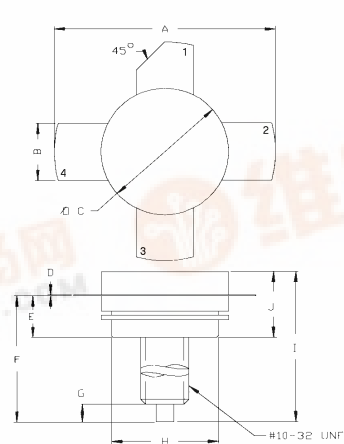
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	8 A
V_{CB}	65 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	1.5 °C/W

PACKAGE STYLE .500 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.050/26,67
B	.220/5,59	.230/5,84
C	.495/12,57	.505/12,83
D	.003/0,08	.007/0,18
E	.160/4,06	.180/4,57
F	.622/15,80	
G	.100/2,54	.130/3,31
H	.415/10,54	.425/10,80
I	.720/18,29	
J	.250/6,35	.290/7,37

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

ORDER CODE: ASI10760

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA			35			V
BV_{CER}	I _C = 50 mA	R _{BE} = 10 Ω		60			V
BV_{CBO}	I _C = 50 mA			65			V
BV_{EBO}	I _E = 10 mA			4.0			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		20		120	---
C_{ob}	V _{CB} = 30 V	f = 1.0 MHz				85	pF
G_{PE}	V _{CE} = 28 V	I _C = 2.5 A	P _{out} = 20 W	8.0	9.0		---
y	f = 225 MHz	VSWR = ∞:1		NO DEGRADATION IN OUTPUT POWER			
IMD₃	V _{CE} = 28 V f = 225 MHz Vision = -8.0 dB	I _C = 2.5 A Snd. = -7.0 dB	P _{ref} = 14 W SB = -16 dB			-55	dB

